AP15G02DF

20V N+P-Channel Enhancement Mode MOSFET

Description

The AP15G02DF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = 20V I_D =15.5A

$R_{DS(ON)}$ < 35mΩ @ V_{GS}=4.5V （**Type：22mΩ**）

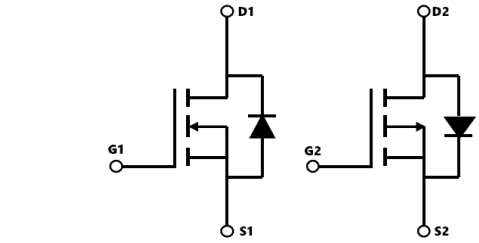
V_{DS} = -20V I_D =-14.8A

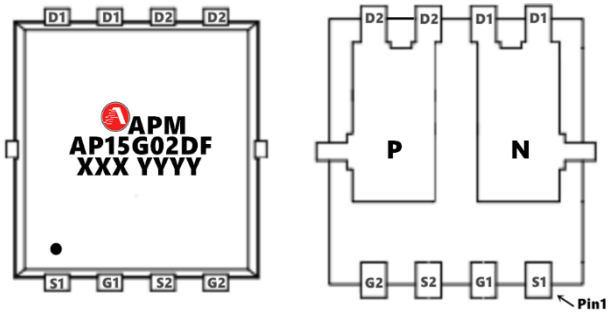
$R_{DS(ON)}$ < 35mΩ @ V_{GS}=-4.5V（**Type：28mΩ**）

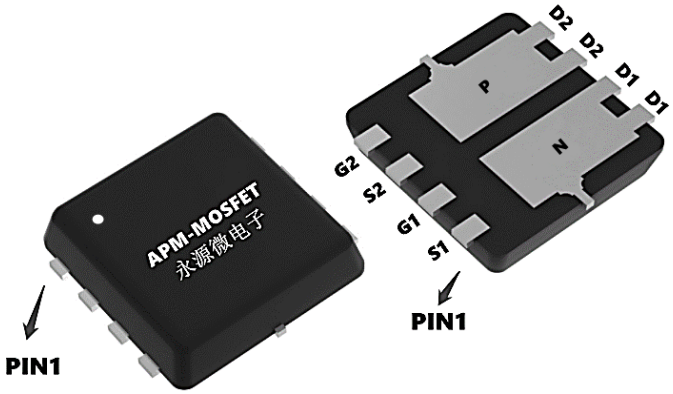
Application

High Frequency Circuit

low-power consumption







Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP15G02DF	PDFN3*3-8L	AP15G02DF XXX YYYY	3000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	N-Ch	P-Ch	Units
V_{DS}	Drain-Source Voltage	20	-20	V
V_{GS}	Gate-Source Voltage	±12	±12	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	15.5	-14.8	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	12.2	-11.5	A
I_{DM}	Pulsed Drain Current[2]	48	-44	A
EAS	Single Pulse Avalanche Energy[3]	24	78	mJ
P_D@T_A=25℃	Total Power Dissipation[4]	1.5		W
T_{STG}	Storage Temperature Range	-55 to 150		℃
T_J	Operating Junction Temperature Range	-55 to 150		℃
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	85		℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	60		℃/W

N-Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	20	22	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=4.5V , I_D=3A	---	22	35	mΩ
		V_{GS}=2.5V , I_D=2A	---	26	40	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	0.5	0.75	1.2	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=16V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=16V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±12V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=3A	---	10.5	---	S
Q_g	Total Gate Charge (4.5V)	V_{DS}=15V , V_{GS}=4.5V , I_D=3A	---	4.6	---	nC
Q_{gs}	Gate-Source Charge		---	0.7	---	
Q_{gd}	Gate-Drain Charge		---	1.5	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=10V , V_{GS}=4.5V , R_G=3.3Ω I_D=3A	---	1.6	---	ns
T_r	Rise Time		---	42	---	
$T_{d(off)}$	Turn-Off Delay Time		---	14	---	
T_f	Fall Time		---	7	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	310	---	pF
C_{oss}	Output Capacitance		---	49	---	
C_{rss}	Reverse Transfer Capacitance		---	35	---	
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	3.6	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :

1、The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The power dissipation is limited by 150℃ junction temperature

4、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

P-Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Units
V(BR)DSS	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-20	-24	-	V
IDSS	Zero Gate Voltage Drain Current	V_{DS}= -20V, V_{GS}=0V,	-	-	-1	μA
IGSS	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±12V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D= -250μA	-0.4	-0.7	-1.0	V
RDS(on)	Static Drain-Source on-Resistance note2	V_{GS}= -4.5V, I_D= -4.1A	-	28	35	mΩ
RDS(on)	Static Drain-Source on-Resistance note2	V_{GS}= -2.5V, I_D= -3A	-	35	42	mΩ
Ciss	Input Capacitance	V_{DS}= -10V, V_{GS}=0V, f=1.0MHz	-	830	-	pF
Coss	Output Capacitance		-	132	-	pF
Crss	Reverse Transfer Capacitance		-	85	-	pF
Q_g	Total Gate Charge	V_{DS}= -10V, I_D= -2A, V_{GS}= -4.5V	-	8.8	-	nC
Qgs	Gate-Source Charge		-	1.4	-	nC
Qgd	Gate-Drain(“Miller”) Charge		-	1.9	-	nC
td(on)	Turn-on Delay Time	V_{DD}= -10V, I_D= -3.3A, R_G= 1Ω, V_{GEN}= -4.5V	-	10	-	ns
tr	Turn-on Rise Time		-	32	-	ns
td(off)	Turn-off Delay Time		-	50	-	ns
t_f	Turn-off Fall Time		-	51	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	-4.1	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-16	A
VSD	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= -4.1A	-	-	-1.2	V

Note :

1、The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The power dissipation is limited by 150℃ junction temperature

4、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

N-Channel Typical Characteristics

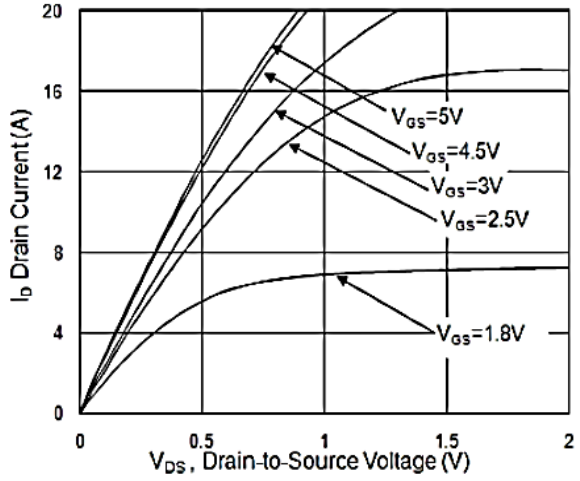


Fig.1 Typical Output Characteristics

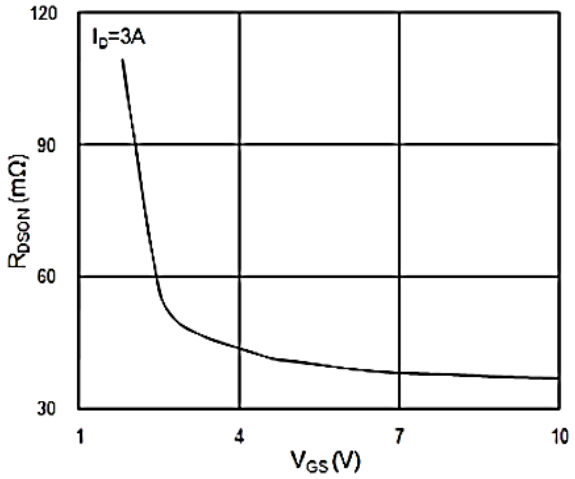


Fig.2 On-Resistance vs. G-S Voltage

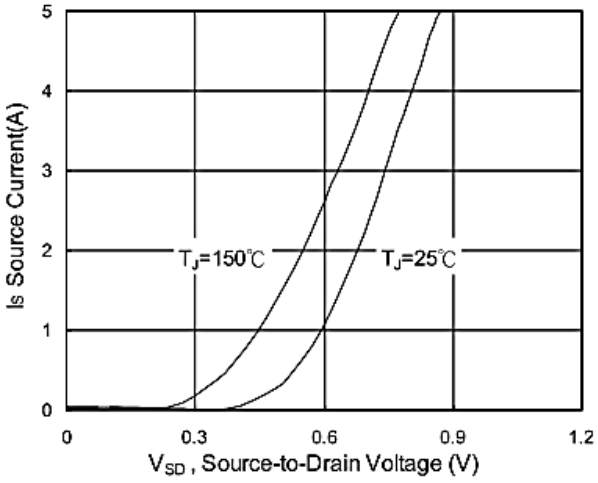


Fig.3 Source Drain Forward Characteristics

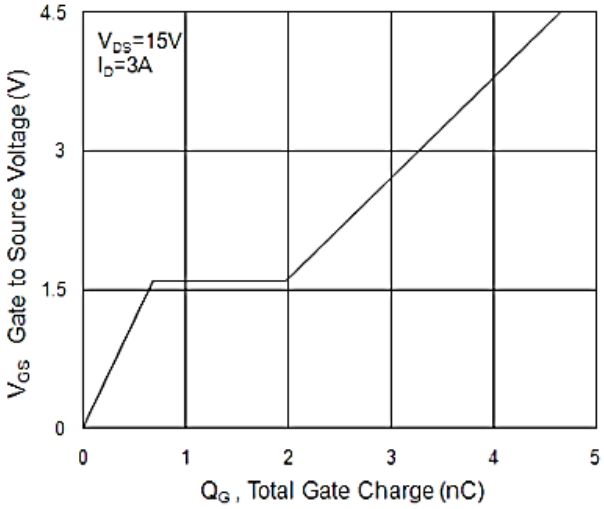


Fig.4 Gate-Charge Characteristics

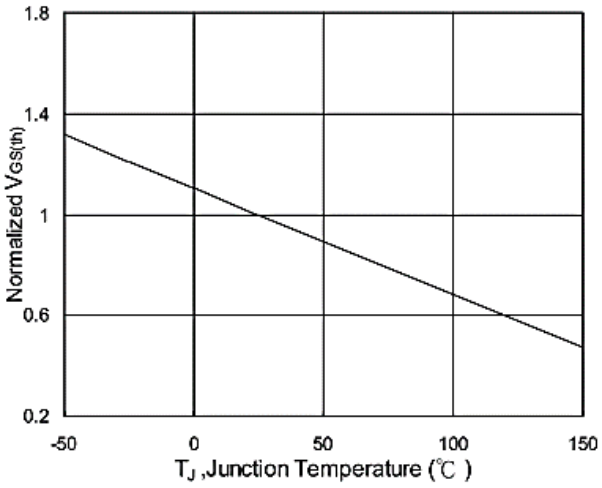


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

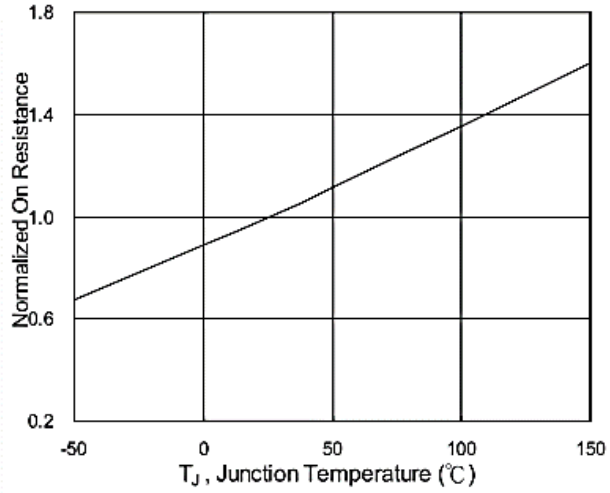


Fig.6 Normalized R_{DSON} vs. T_J

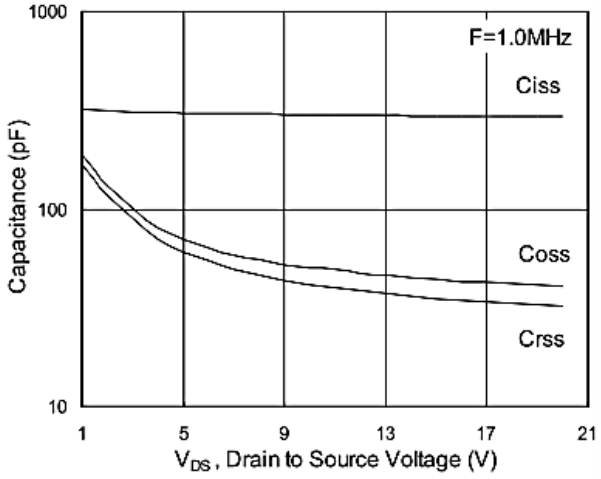


Fig.7 Capacitance

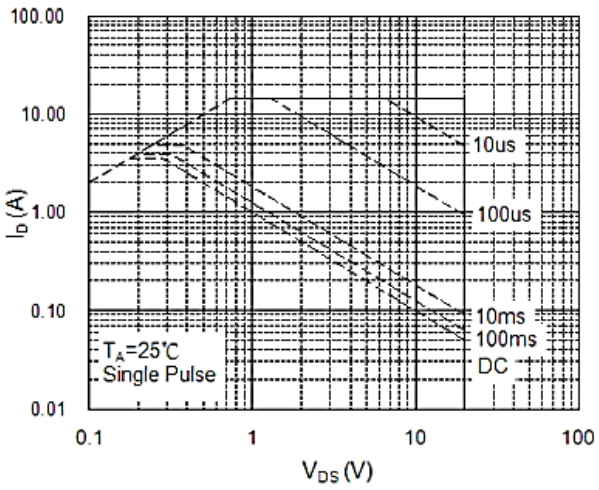


Fig.8 Safe Operating Area

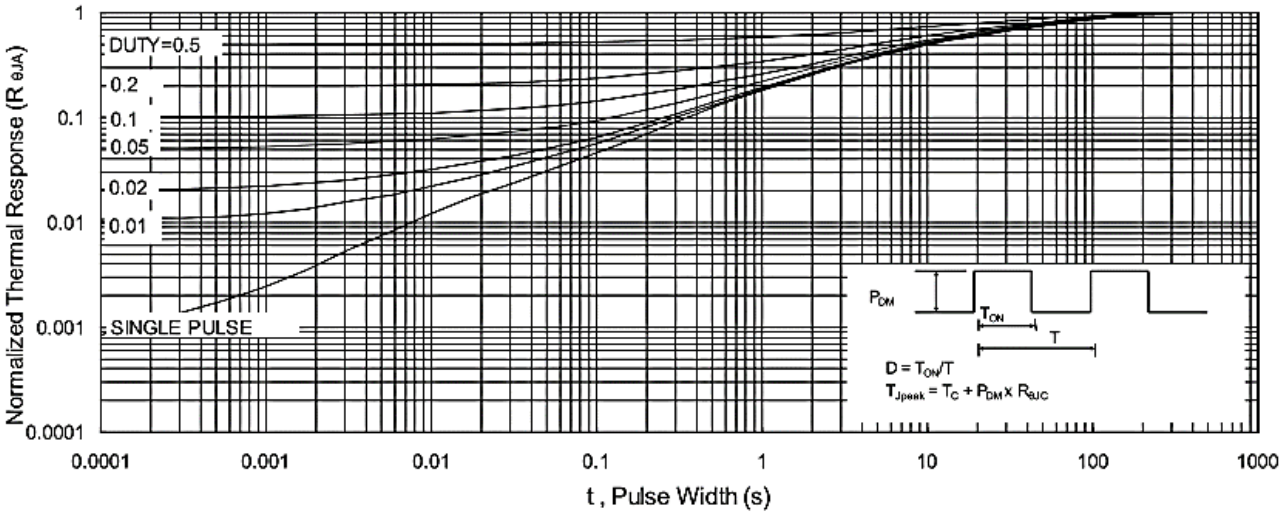


Fig.9 Normalized Maximum Transient Thermal Impedance

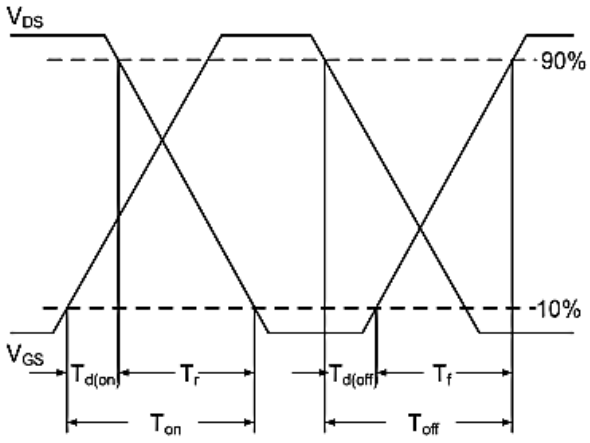


Fig.10 Switching Time Waveform

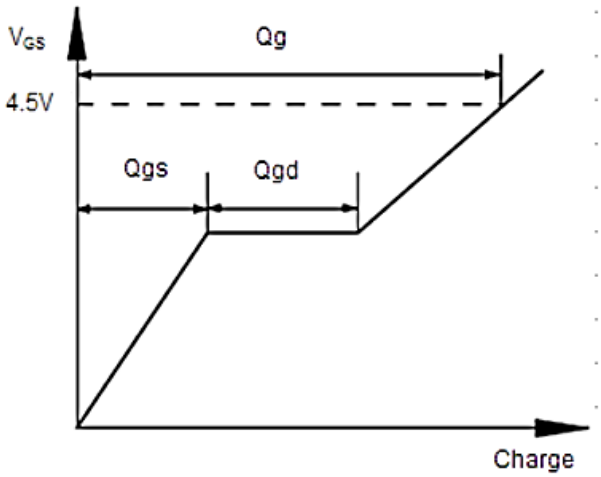


Fig.11 Gate Charge Waveform

P-Channel Typical Characteristics

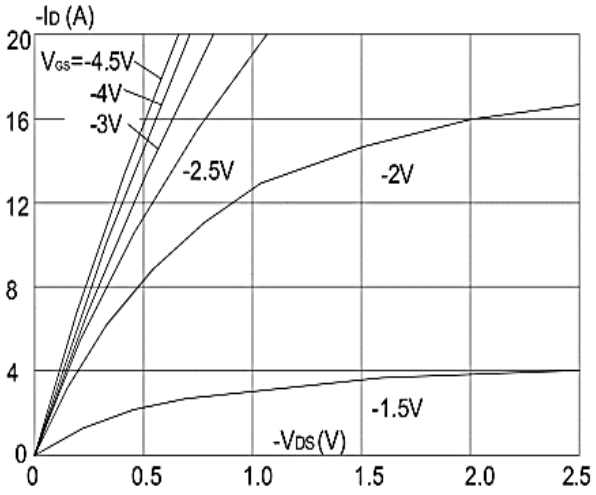


Figure1: Output Characteristics

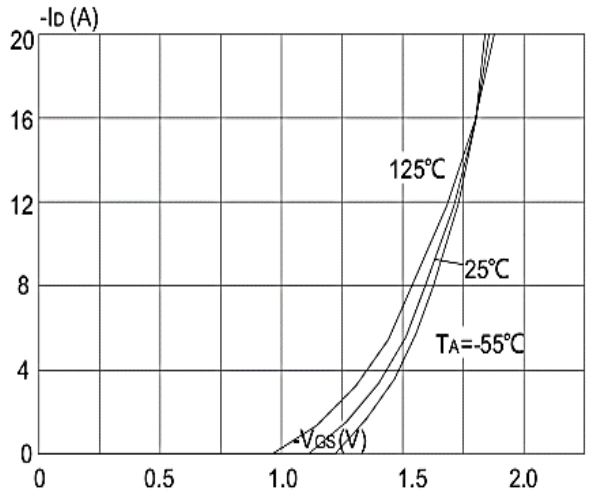


Figure 2: Typical Transfer Characteristics

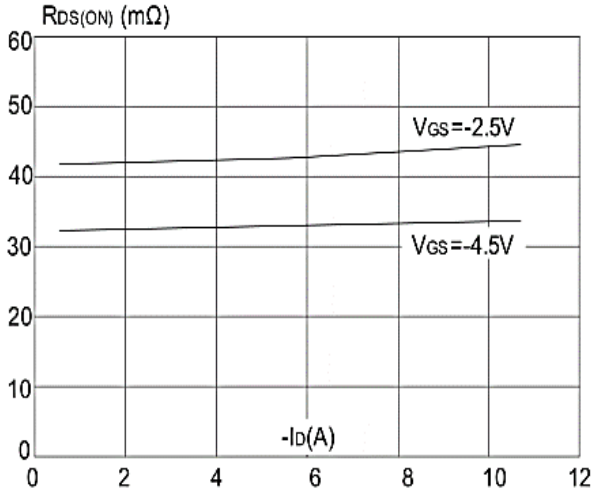


Figure 3:On-resistance vs. Drain Current

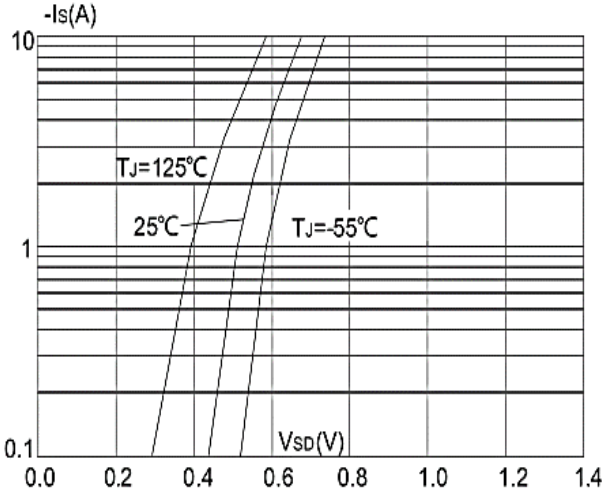


Figure 4: Body Diode Characteristics

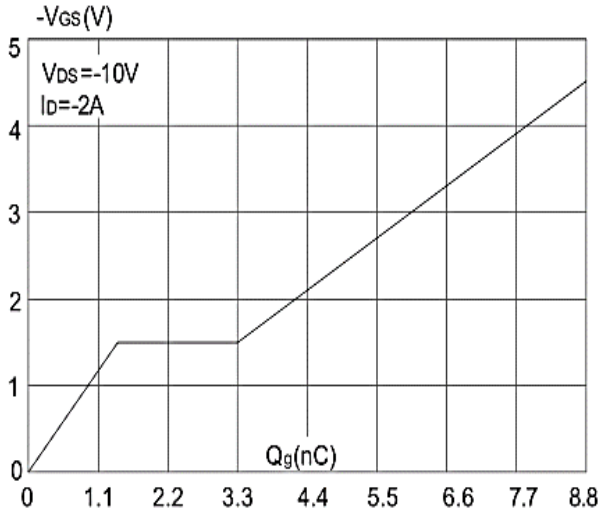


Figure 5: Gate Charge Characteristics

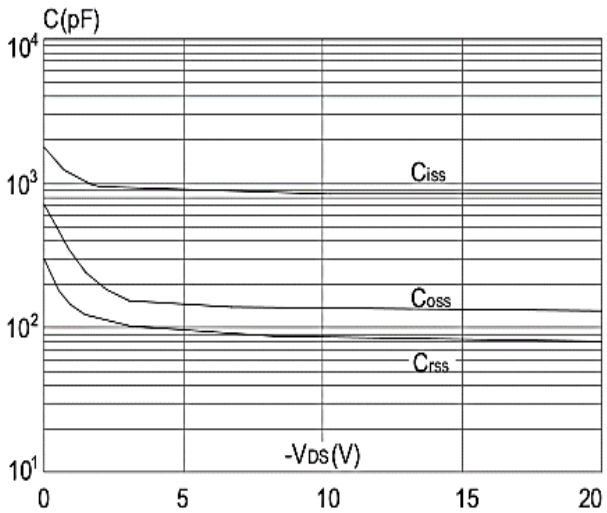


Figure 6: Capacitance Characteristics

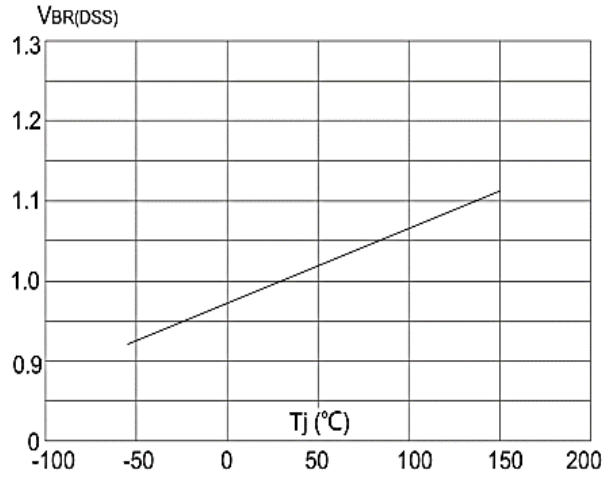


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

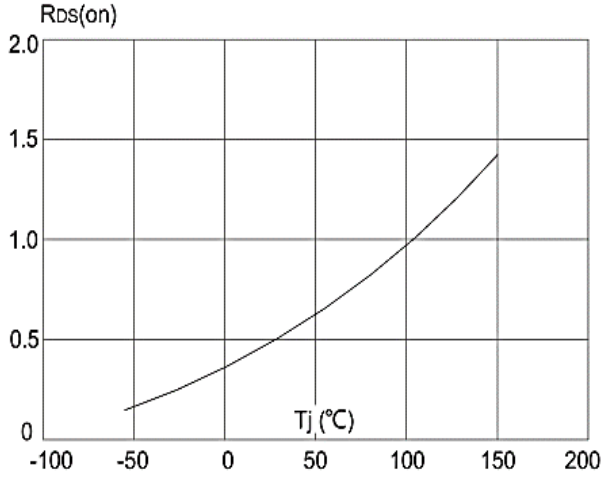


Figure 8: Normalized on Resistance vs. Junction Temperature

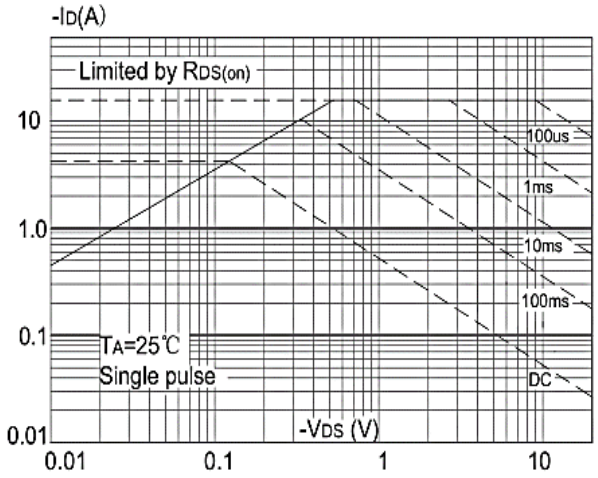


Figure 9: Maximum Safe Operating Area

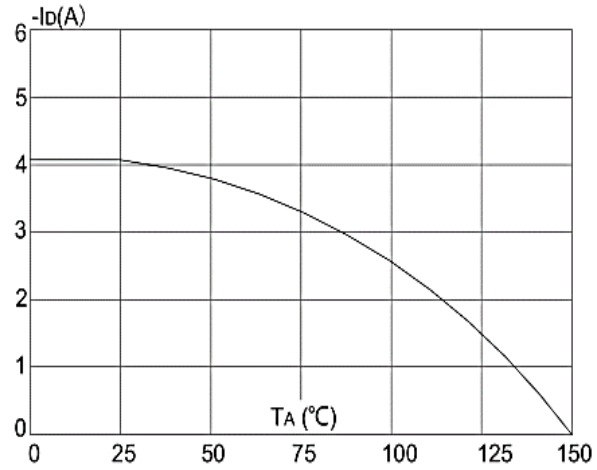


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

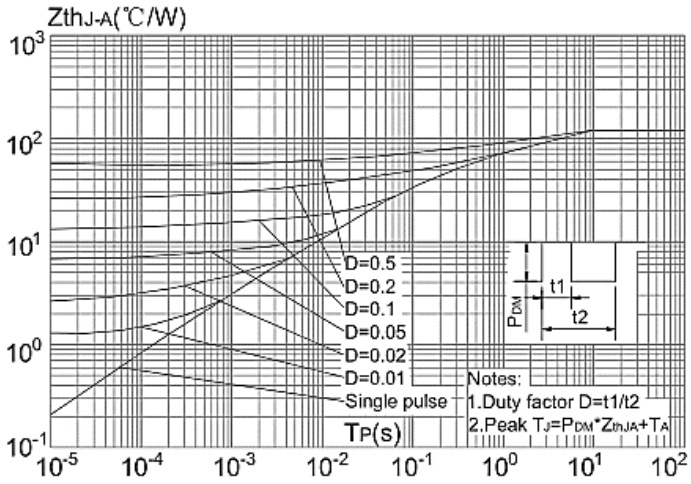
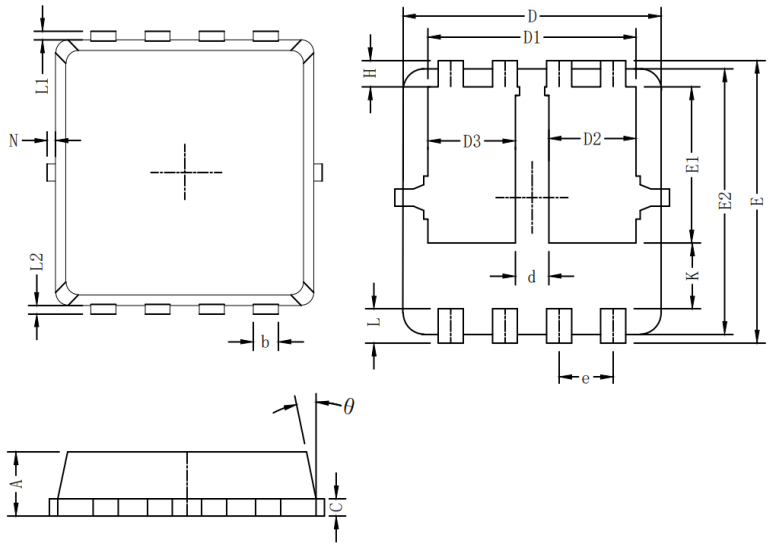


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Package Mechanical Data-PDFN3*3-8L-Double



Symbol	Dim in mm		
	Min	Typ	Max
A	0.6	0.75	0.9
b	0.2	0.3	0.4
C	0.15	0.2	0.25
D	3	3.1	3.2
D1	2.3	2.45	2.6
D2/D3	0.8	1	1.2
E	3.15	3.3	3.45
E1	1.43	1.73	1.93
E2	2.9	3.05	3.2
e	0.65BSC		
H	0.2	0.35	0.5
K	0.57	0.77	0.87
L	0.3	0.4	0.5
L1/L2	0.1REF		
θ	8°	10°	13°
N	0		0.15
d	0.3	0.4	0.5

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Edition	Date	Change
REV1.0	2024/1/21	Initial release